PRELIMINARY

SFF100N10M
SFF100N10Z

SOLID STATE DEVICES, INC

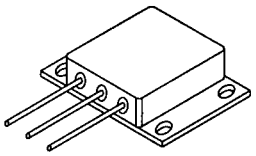
14849 Firestone Boulevard · La Mirada,CA 90638
Phone: (714) 670-SSDI (7734) · Fax: (714) 522-7424

Designer's Data Sheet

100 AMP
100 VOLTS
0.015Ω
N-CHANNEL
POWER MOSFET

FEATURES:

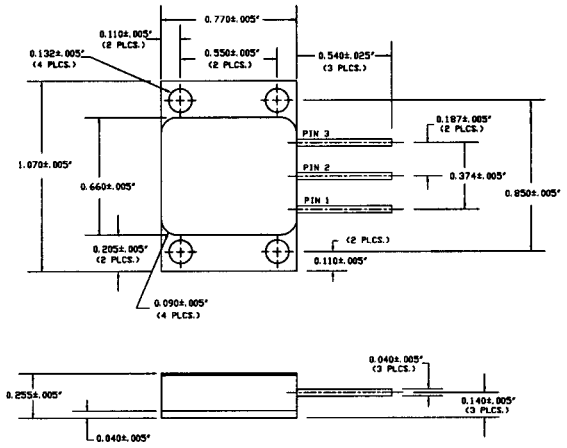
- Rugged construction with poly silicon gate
- Low RDS(on) and high transconductance
- Excellent high temperature stability
- Very fast switching speed
- Fast recovery and superior dv/dt performance
- Increased reverse energy capability
- Low input and transfer capacitance for easy paralleling
- Hermetically sealed surface mount power package
- TX, TXV and Space Level screening available
- Replaces: IRF340 Types



MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	VALUE	UNIT
Drain to Source Voltage	V_{DS}	100	Volts
Gate to Source Voltage	V_{GS}	±20	Volts
Continuous Drain Current	I_D	100	Amps
Operating and Storage Temperature	T_{op} & T_{stg}	-55 to +150	°C
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.42	°C/W
Total Device Dissipation @ TC=25°C Total Device Dissipation @ TC=55°C	P_D	300 200	Watts
Repetitive Avalanche Energy	EAS	30	mJ

PACKAGE OUTLINE: 3 PIN POWER PACK



NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: F00309 A

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ELECTRICAL CHARACTERISTICS @ TJ=25°C (Unless Otherwise Specified)

RATING		SYMBOL	MIN	TYP	MAX	UNIT
Drain to Source Breakdown Voltage (VGS=0 V, ID=250μA)		BV_{DSS}	100	---	---	V
Drain to Source on State Resistance (VGS=10 V, ID=50% Rated ID)		$R_{DS(on)}$	---	---	0.015	Ω
On State Drain Current (VDS>ID(on) X RDS(on) Max, VGS=10 V)		$I_{D(on)}$	100	---	---	V/°C
Gate Threshold Voltage (VDS≥VGS, ID=4mA)		$V_{GS(th)}$	2.0	---	4.0	V
Forward Transconductance (VDS>ID(on) X RDS(on) Max, IDS=50% rated ID)		g_{fs}	30	49	---	S(℧)
Zero Gate Voltage Drain Current (VDS=max rated voltage, VGS=0 V) (VDS=80% rated VDS, VGS=0 V, TA=125°C)		I_{DSS}	--- ---	--- ---	10 200	μA
Gate to Source Leakage Forward **Gate to Source Leakage Reverse**	At rated VGS	I_{GSS}	--- ---	--- ---	+200 -200	nA
Total Gate Charge **Gate to Source Charge** **Gate to Drain Charge**	VGS=10 Volts 50% rated VDS 50% rated ID	Q_g Q_{gs} Q_{gd}	--- --- ---	380 45 150	--- --- ---	nC
Turn on Delay Time **Rise Time** **Turn Off Delay Time** **Fall Time**	VDD= 50% rated VDS 50% rated ID RG=6.2 Ω VGS=10V	$t_{d(on)}$ t_r $t_{d(off)}$ t_f	--- --- --- ---	48 490 190 380	196 980 380 770	nsec
Diode Forward Voltage (IS=rated ID, VGS=0 V, TJ=25°C)		V_{SD}	---	---	1.6	V
Diode Reverse Recovery Time **Reverse Recovery Charge**	TJ=25°C IF=10A di/dt=100 A/μsec	t_{rr} Q_{RR}	--- ---	--- 2.34	200 ---	nsec μC
Input Capacitance **Output Capacitance** **Reverse Transfer Capacitance**	VGS=0 Volts VDS=25 Volts f= 1 MHz	C_{iss} C_{oss} C_{rss}	--- --- ---	7600 3300 1200	10640 4630 2400	pF

For thermal derating curves and other characteristic curves please contact SSDI Marketing Department.